

TECHNICAL DATA
DATA SHEET 250, REV. D

HERMETIC POWER SCHOTTKY RECTIFIER 175°C Maximum Operation Temperature

DESCRIPTION: A 100 VOLT, 120 AMP, HERMETIC POWER SCHOTTKY RECTIFIER IN A SHD-3/3B PACKAGE.

MAXIMUM RATINGS SPECIFIED.

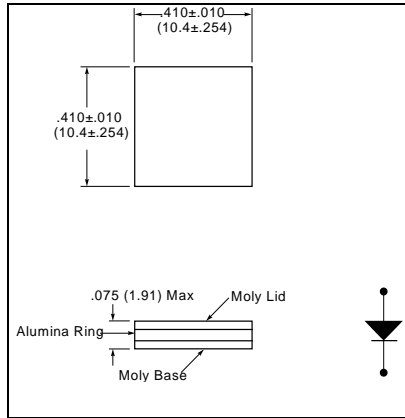
ALL RATINGS ARE @ $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	100	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100^\circ\text{C}$)	I_O	120	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t=10\text{ms}$, Sine)	I_{FSM}	1650	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_r=5\text{V}$)	C_T	3000	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R\theta_{JC}$	0.38	$^\circ\text{C/W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to + 175	$^\circ\text{C}$

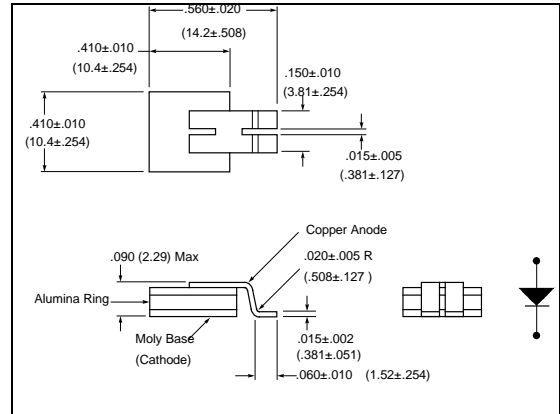
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 120$ Amps)			
$T_J = 25^\circ\text{C}$	V_f	0.87	Volts
$T_J = 125^\circ\text{C}$		0.72	
MAXIMUM REVERSE CURRENT (I_r @ 100 V PIV)			
$T_J = 25^\circ\text{C}$	I_r	2.0	mA
$T_J = 125^\circ\text{C}$		48	

MECHANICAL DIMENSIONS: In Inches / mm

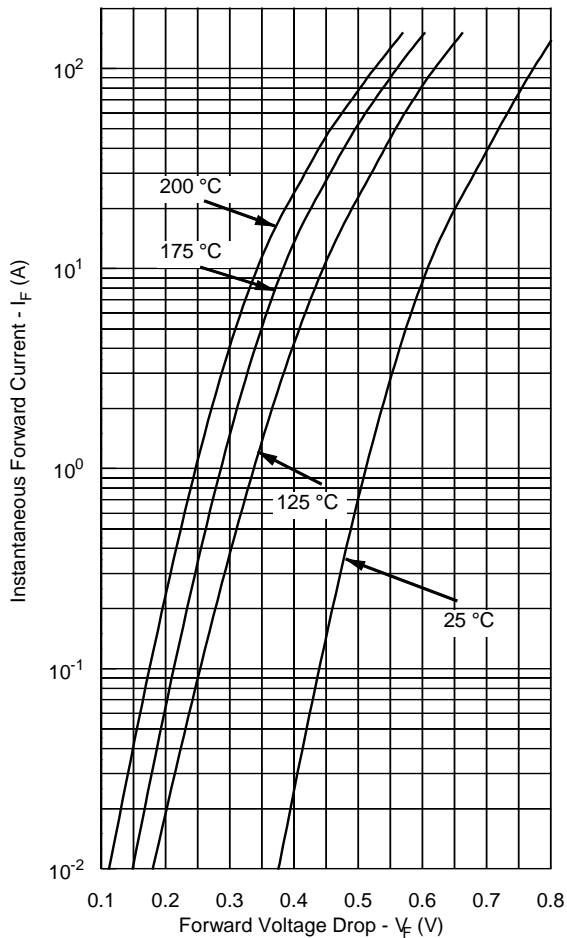


SHD-3

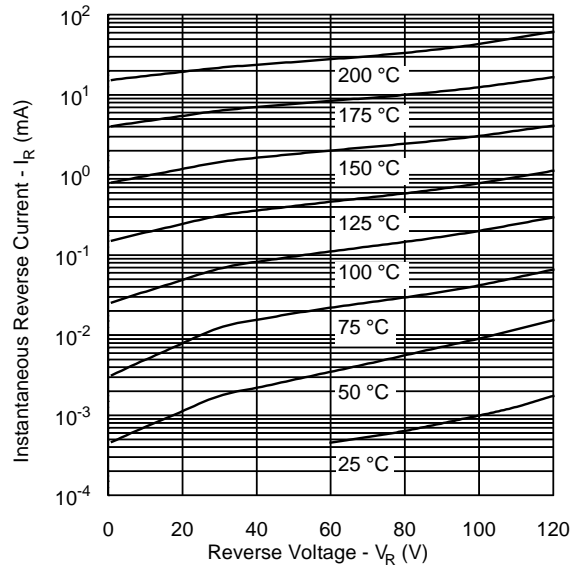


SHD-3B

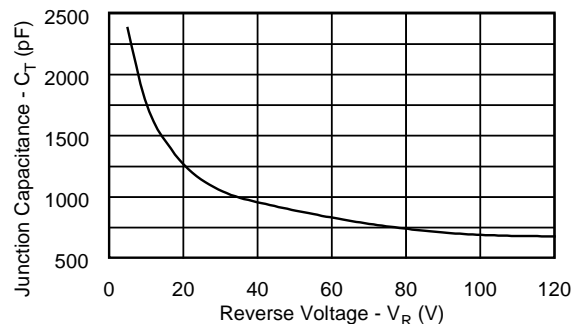
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



SENSITRON
DATA SHEET 250, REV. E

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